

# RJH60F7DPQ-A0

Silicon N Channel IGBT  
High Speed Power Switching

R07DS0328EJ0100

Rev.1.00

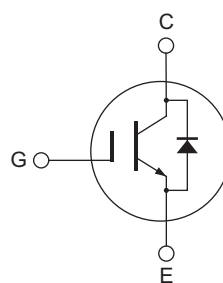
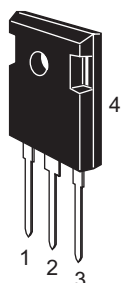
Apr 06, 2011

## Features

- Low collector to emitter saturation voltage  
 $V_{CE(sat)} = 1.35 \text{ V typ. (at } I_C = 50 \text{ A, } V_{GE} = 15 \text{ V, } T_a = 25^\circ\text{C)}$
- Built in fast recovery diode in one package
- Trench gate and thin wafer technology
- High speed switching  
 $t_f = 74 \text{ ns typ. (at } I_C = 30 \text{ A, } V_{CE} = 400 \text{ V, } V_{GE} = 15 \text{ V, } R_g = 5 \Omega, T_a = 25^\circ\text{C, inductive load)}$

## Outline

RENESAS Package code: PRSS0003ZH-A  
(Package name: TO-247A)



1. Gate
2. Collector
3. Emitter
4. Collector

## Absolute Maximum Ratings

( $T_c = 25^\circ\text{C}$ )

| Item  | Symbol                          | Ratings     | Unit               |   |
|---|---------------------------------|-------------|--------------------|---|
| Collector to emitter voltage                    | $V_{CES}$                       | 600         | V                  |   |
| Gate to emitter voltage                         | $V_{GES}$                       | $\pm 30$    | V                  |   |
| Collector current                               | $T_c = 25^\circ\text{C}$        | $I_C$       | 90                 | A |
|   | $T_c = 100^\circ\text{C}$       | $I_C$       | 50                 | A |
| Collector peak current                          | $i_{c(peak)}$ <sup>Note1</sup>  | 180         | A                  |   |
| Collector to emitter diode forward peak current | $i_{DF(peak)}$ <sup>Note2</sup> | 100         | A                  |   |
| Collector dissipation                           | $P_C$                           | 328.9       | W                  |   |
| Junction to case thermal impedance (IGBT)       | $\theta_{j-c}$                  | 0.38        | $^\circ\text{C/W}$ |   |
| Junction to case thermal impedance (Diode)      | $\theta_{j-cd}$                 | 2.0         | $^\circ\text{C/W}$ |   |
| Junction temperature                            | $T_j$                           | 150         | $^\circ\text{C}$   |   |
| Storage temperature                             | $T_{stg}$                       | -55 to +150 | $^\circ\text{C}$   |   |

Notes: 1. Pulse width limited by safe operating area.

2.  $PW \leq 5 \mu\text{s}$ , duty cycle  $\leq 1\%$

## Electrical Characteristics

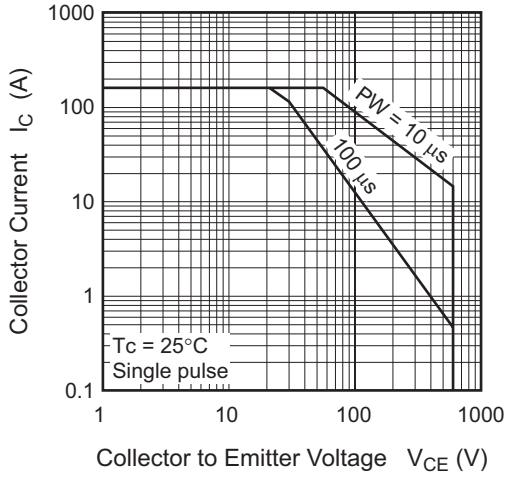
(T<sub>j</sub> = 25°C)

| Item                                    | Symbol               | Min | Typ  | Max  | Unit | Test Conditions  |
|---|----------------------|-----|------|------|------|--|
| Zero gate voltage collector current     | I <sub>CES</sub>     | —   | —    | 100  | μA   | V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0  |
| Gate to emitter leak current            | I <sub>GES</sub>     | —   | —    | ±1   | μA   | V <sub>GE</sub> = ±30 V, V <sub>CE</sub> = 0   |
| Gate to emitter cutoff voltage          | V <sub>GE(off)</sub> | 4   | —    | 8    | V    | V <sub>CE</sub> = 10V, I <sub>C</sub> = 1 mA   |
| Collector to emitter saturation voltage | V <sub>CE(sat)</sub> | —   | 1.35 | 1.75 | V    | I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15V <sup>Note3</sup>  |
|   | V <sub>CE(sat)</sub> | —   | 1.6  | —    | V    | I <sub>C</sub> = 90 A, V <sub>GE</sub> = 15V <sup>Note3</sup>  |
| Input capacitance                       | C <sub>ies</sub>     | —   | 4700 | —    | pF   | V <sub>CE</sub> = 25 V   |
| Output capacitance                      | C <sub>oes</sub>     | —   | 198  | —    | pF   | V <sub>GE</sub> = 0 V  |
| Reverse transfer capacitance            | C <sub>res</sub>     | —   | 83   | —    | pF   | f = 1 MHz  |
| Switching time                          | t <sub>d(on)</sub>   | —   | 63   | —    | ns   | I <sub>C</sub> = 30 A,<br>V <sub>CE</sub> = 400 V, V <sub>GE</sub> = 15 V<br>R <sub>g</sub> = 5 Ω <sup>Note3</sup><br>Inductive load |
|   | t <sub>r</sub>       | —   | 81   | —    | ns   |  |
|   | t <sub>d(off)</sub>  | —   | 142  | —    | ns   |  |
|   | t <sub>f</sub>       | —   | 74   | —    | ns   |  |
| C-E diode forward voltage               | V <sub>ECF1</sub>    | —   | 1.2  | 2.1  | V    | I <sub>F</sub> = 20 A <sup>Note3</sup>   |
|   | V <sub>ECF2</sub>    | —   | 1.5  | —    | V    | I <sub>F</sub> = 40 A <sup>Note3</sup>   |
| C-E diode reverse recovery time         | t <sub>rr</sub>      | —   | 90   | —    | ns   | I <sub>F</sub> = 20 A<br>di <sub>F</sub> /dt = 100 A/μs  |

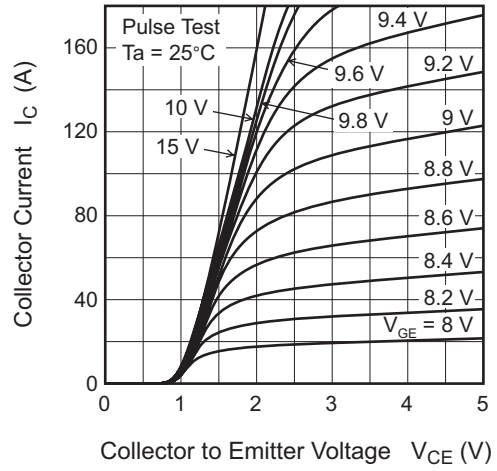
Notes: 3. Pulse test

# Main Characteristics

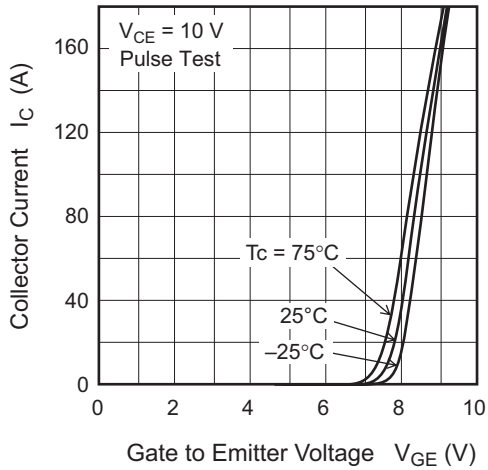
Maximum Safe Operation Area



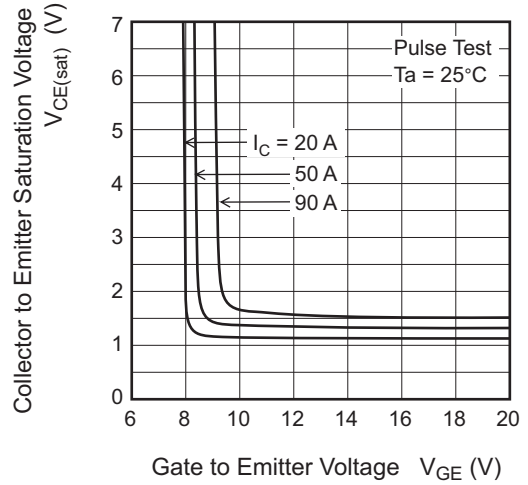
Typical Output Characteristics



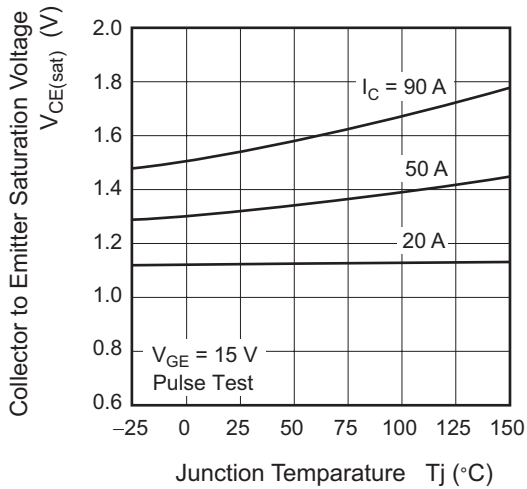
Typical Transfer Characteristics



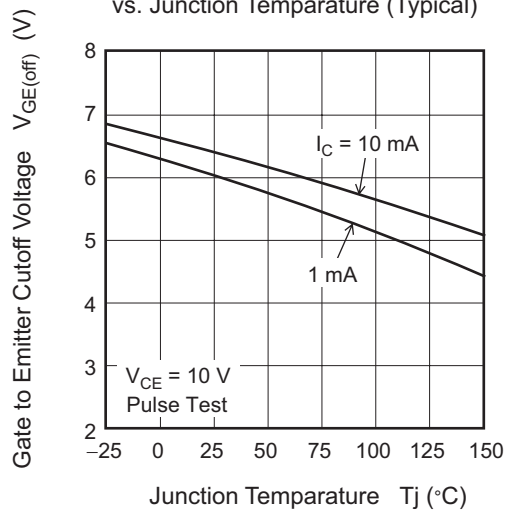
Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage (Typical)



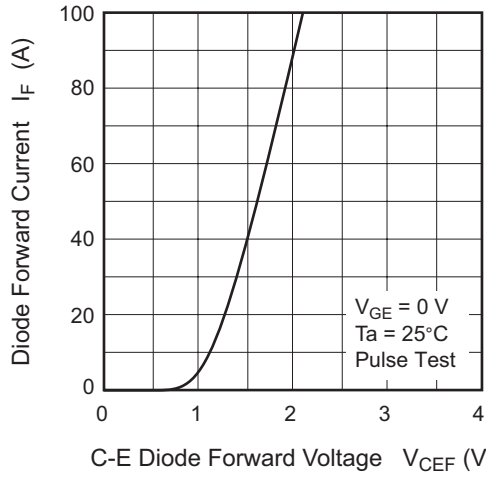
Collector to Emitter Saturation Voltage vs. Junction Temperature (Typical)



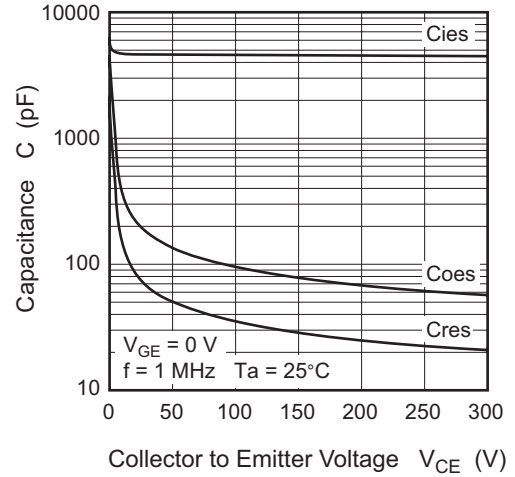
Gate to Emitter Cutoff Voltage vs. Junction Temperature (Typical)



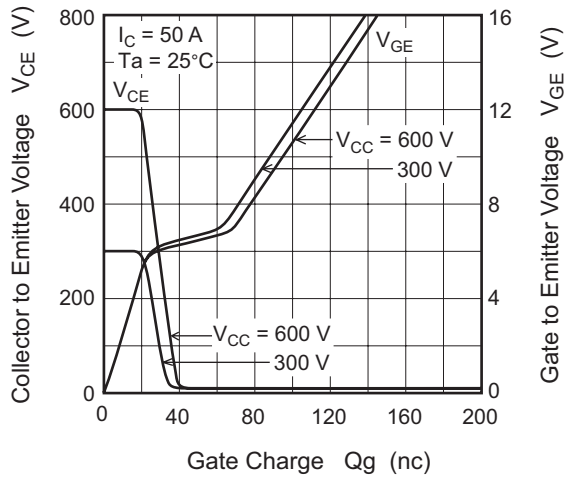
Forward Current vs. Forward Voltage (Typical)



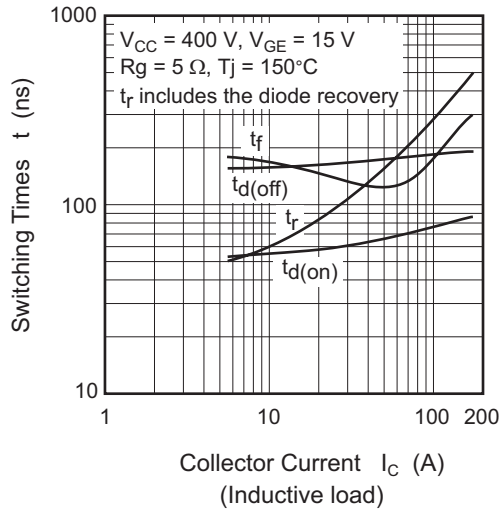
Typical Capacitance vs. Collector to Emitter Voltage



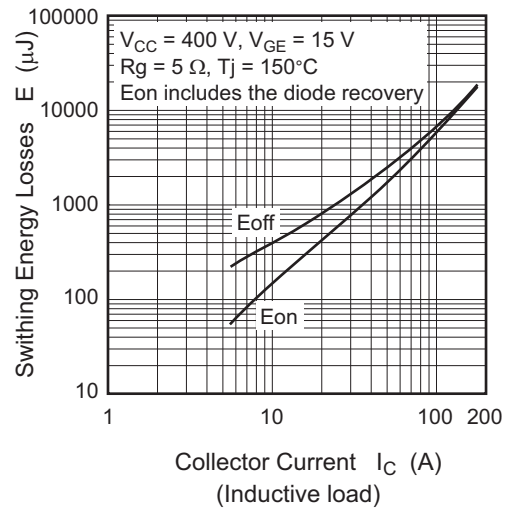
Dynamic Input Characteristics (Typical)



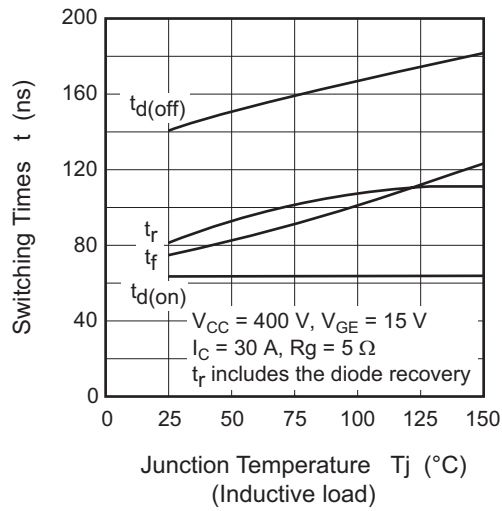
Switching Characteristics (Typical) (1)



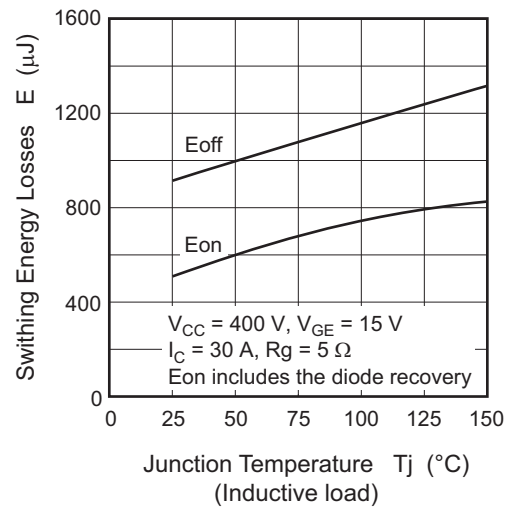
Switching Characteristics (Typical) (2)

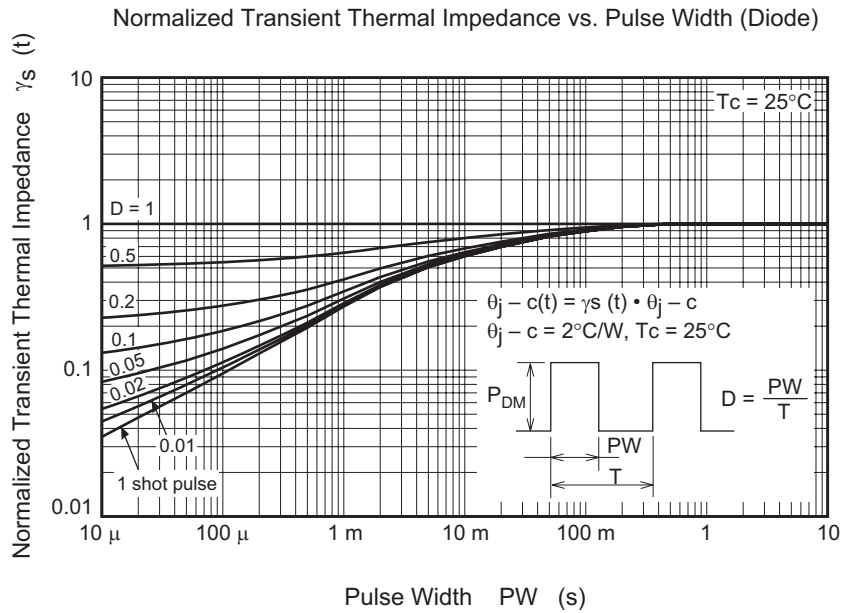
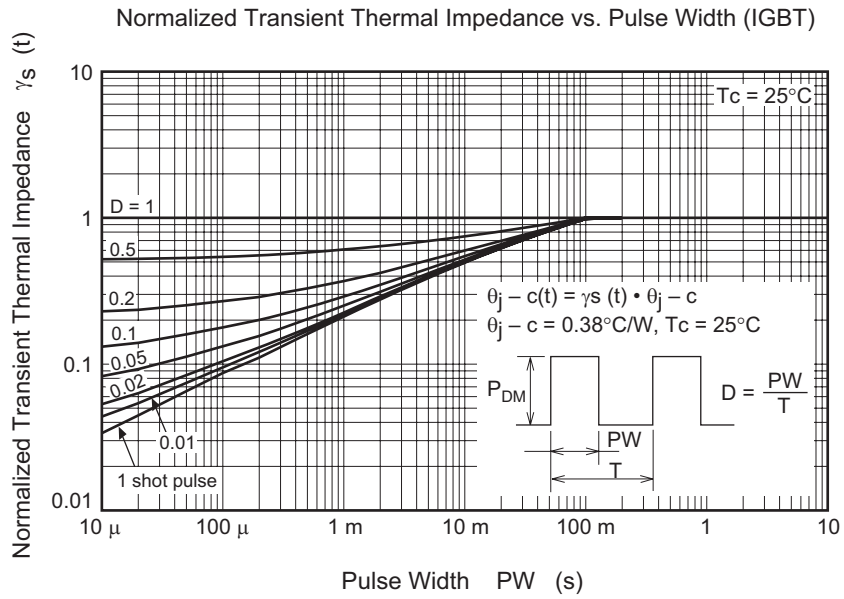


Switching Characteristics (Typical) (3)

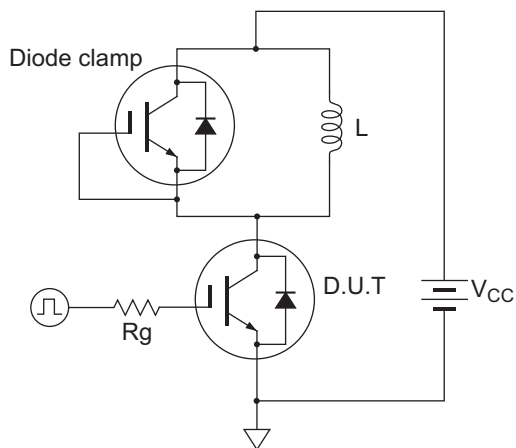


Switching Characteristics (Typical) (4)

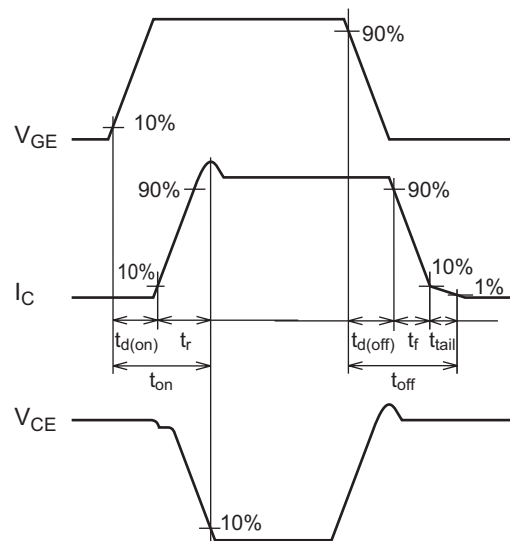




Switching Time Test Circuit



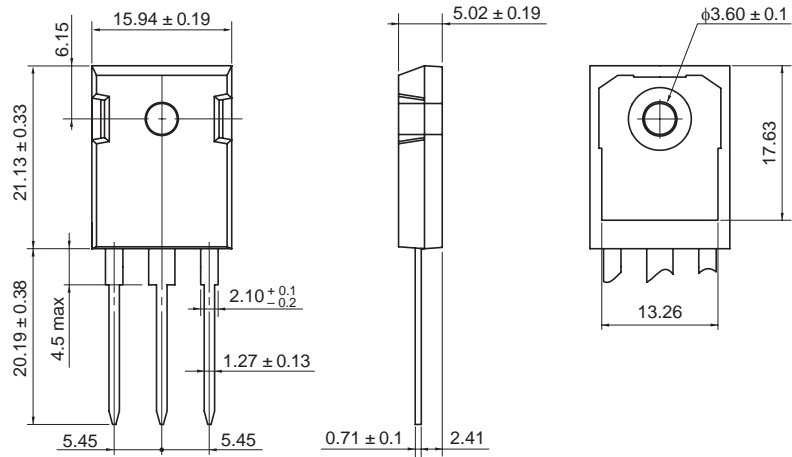
Waveform



## Package Dimensions

|              |                    |              |               |            |
|--------------|--------------------|--------------|---------------|------------|
| Package Name | JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] |
| TO-247A      | —                  | PRSS0003ZH-A | —             | 6.14g      |

Unit: mm



## Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJH60F7DPQ-A0-T0      | 240 pcs  | Box (Tube)         |

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**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
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**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-585-100, Fax: +44-1628-585-900

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
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